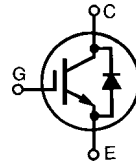


Preliminary data

# HiPerFAST™ IGBT with Diode Combi Pack

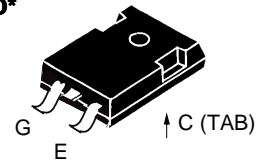
## IXGH22N50BU1 IXGH22N50BU1S

$V_{CES}$	=	500 V
$I_{C(25)}$	=	44 A
$V_{CE(sat)typ}$	=	2.1 V
$t_{fi(typ)}$	=	55 ns

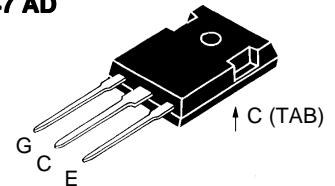


Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	500	V
$V_{CGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GE} = 1\text{ M}\Omega$	500	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ\text{C}$	44	A
$I_{C90}$	$T_C = 90^\circ\text{C}$	22	A
$I_{CM}$	$T_C = 25^\circ\text{C}$ , 1 ms	88	A
<b>SSOA (RBSOA)</b>	$V_{GE} = 15\text{ V}$ , $T_{VJ} = 125^\circ\text{C}$ , $R_G = 22\ \Omega$ Clamped inductive load, $L = 100\ \mu\text{H}$	$I_{CM} = 44$ @ $0.8 V_{CES}$	A
$P_C$	$T_C = 25^\circ\text{C}$	150	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
Maximum Lead and Tab temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
$M_d$	Mounting torque, TO-247 AD	1.13/10	Nm/lb.in.
<b>Weight</b>	TO-247 SMD	4	g
	TO-247 AD	6	g

### TO-247 SMD\*



### TO-247 AD



G = Gate, C = Collector,  
E = Emitter, TAB = Collector

\*Add suffix letter "S" for surface mountable package

### Features

- International standard packages  
JEDEC TO-247 SMD surface mountable and JEDEC TO-247 AD
- High frequency IGBT and antiparallel FRED in one package
- High current handling capability
- HiPerFAST™ HDMOS™ process
- MOS Gate turn-on  
- drive simplicity

### Applications

- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies
- AC motor speed control
- DC servo and robot drives
- DC choppers

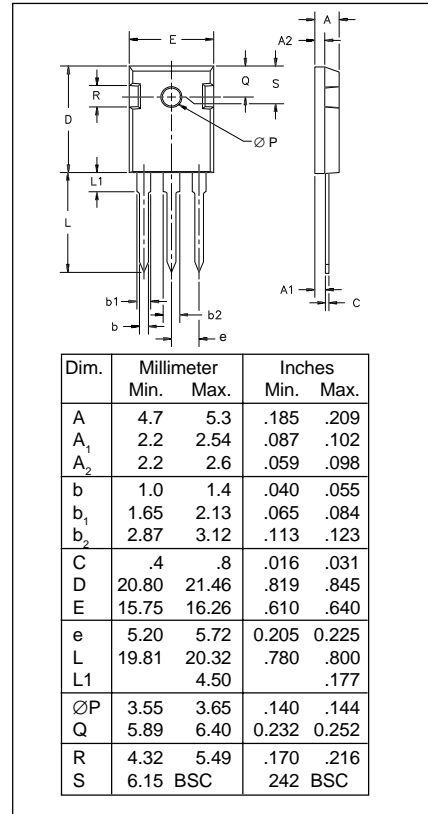
### Advantages

- Space savings (two devices in one package)
- High power density
- Suitable for surface mounting
- Very low switching losses for high frequency applications
- Easy to mount with 1 screw, TO-247 (insulated mounting screw hole)

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$BV_{CES}$	$I_C = 250\ \mu\text{A}$ , $V_{GE} = 0\text{ V}$	500		V
$V_{GE(th)}$	$I_C = 250\ \mu\text{A}$ , $V_{CE} = V_{GE}$	2.5		V
$I_{CES}$	$V_{CE} = 0.8 \cdot V_{CES}$			200 $\mu\text{A}$
	$V_{GE} = 0\text{ V}$			8 mA
$I_{GES}$	$V_{CE} = 0\text{ V}$ , $V_{GE} = \pm 20\text{ V}$			$\pm 100\text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}$ , $V_{GE} = 15\text{ V}$	2.1	2.5	V

Symbol	Test Conditions	Characteristic Values		
		(T <sub>J</sub> = 25°C, unless otherwise specified)		
		min.	typ.	max.
<b>g<sub>fs</sub></b>	I <sub>C</sub> = I <sub>C90</sub> ; V <sub>CE</sub> = 10 V, Pulse test, t ≤ 300 μs, duty cycle ≤ 2 %	9	16	S
<b>C<sub>ies</sub></b> <b>C<sub>oes</sub></b> <b>C<sub>res</sub></b>	V <sub>CE</sub> = 25 V, V <sub>GE</sub> = 0 V, f = 1 MHz		1450	pF
			120	pF
			37	pF
<b>Q<sub>gc</sub></b> <b>Q<sub>ge</sub></b> <b>Q<sub>gs</sub></b>	I <sub>C</sub> = I <sub>C90</sub> , V <sub>GE</sub> = 15 V, V <sub>CE</sub> = 0.5 V <sub>CES</sub>		90	nC
			11	nC
			30	nC
<b>t<sub>d(on)</sub></b> <b>t<sub>ri</sub></b> <b>t<sub>on</sub></b> <b>t<sub>d(off)</sub></b> <b>t<sub>off</sub></b>	<b>Inductive load, T<sub>J</sub> = 25°C</b> I <sub>C</sub> = I <sub>C90</sub> , V <sub>GE</sub> = 15 V, L = 100 μH, V <sub>CE</sub> = 0.8 V <sub>CES</sub> , R <sub>G</sub> = R <sub>off</sub> = 10 Ω		15	ns
			30	ns
		0.15		mJ
		100	150	ns
		55	110	ns
	Note 1	0.3	0.5	mJ
<b>t<sub>d(on)</sub></b> <b>t<sub>ri</sub></b> <b>t<sub>on</sub></b> <b>t<sub>d(off)</sub></b> <b>t<sub>off</sub></b>	<b>Inductive load, T<sub>J</sub> = 125°C</b> I <sub>C</sub> = I <sub>C90</sub> , V <sub>GE</sub> = 15 V, L = 100 μH, V <sub>CE</sub> = 0.8 V <sub>CES</sub> , R <sub>G</sub> = R <sub>off</sub> = 10 Ω		15	ns
			30	ns
		0.15		mJ
		140		ns
		100		ns
	Note 1	0.6		mJ
<b>R<sub>thJC</sub></b> <b>R<sub>thCK</sub></b>				0.83 K/W K/W
		0.25		

### TO-247 AD Outline

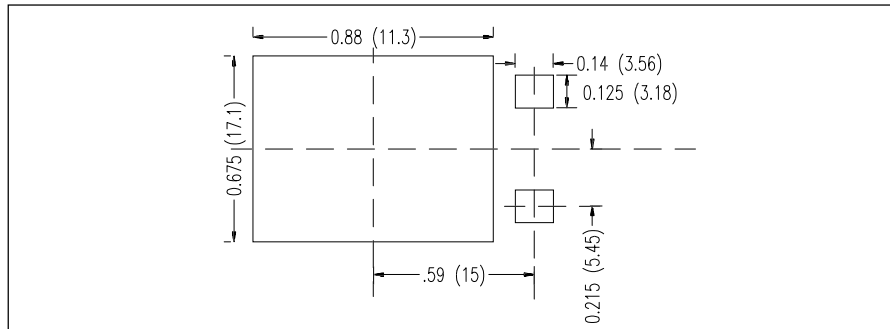


### Reverse Diode (FRED)

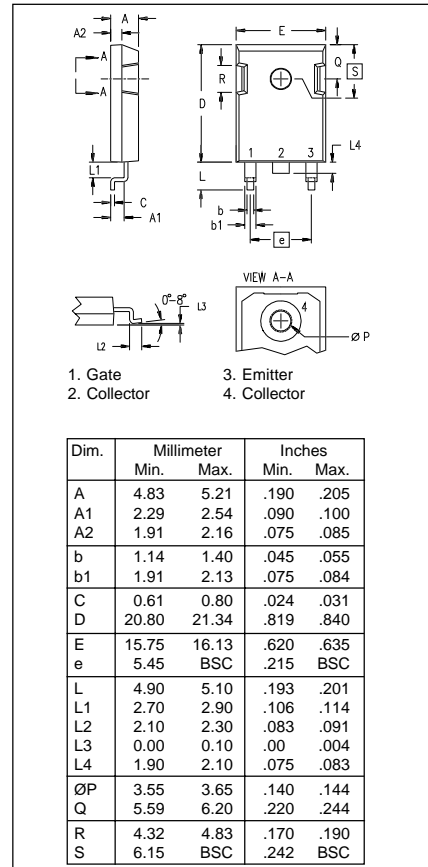
Symbol	Test Conditions	Characteristic Values		
		(T <sub>J</sub> = 25°C, unless otherwise specified)		
		min.	typ.	max.
<b>V<sub>F</sub></b>	I <sub>F</sub> = I <sub>C90</sub> , V <sub>GE</sub> = 0 V, Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			1.6 V
<b>I<sub>RM</sub></b> <b>t<sub>rr</sub></b>	I <sub>F</sub> = I <sub>C90</sub> , V <sub>GE</sub> = 0 V, -di <sub>F</sub> /dt = 240 A/μs V <sub>R</sub> = 360 V T <sub>J</sub> = 125°C I <sub>F</sub> = 1 A; -di <sub>F</sub> /dt = 100 A/μs; V <sub>R</sub> = 30 V T <sub>J</sub> = 25°C		10	15 A
			150	ns
			35	50
<b>R<sub>thJC</sub></b>				1 K/W

Note 1: Switching times may increase for V<sub>CE</sub> (Clamp) > 0.8 • V<sub>CES</sub>, higher T<sub>J</sub> or increased R<sub>G</sub>

### Min. Recommended Footprint (Dimensions in inches and mm)



### TO-247 SMD Outline



IXYS reserves the right to change limits, test conditions, and dimensions.